

App. No.: 10/695,969

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AMENDMENTS TO THE CLAIMS

AUG 21 2006

The following listing of claims replaces all prior listings of claims in the present application.

What is claimed is:

1. (Previously Presented) A semiconductor integrated circuit, comprising:
 - a silicon substrate;
 - a silicon epitaxial layer that touches the surface of said silicon substrate and has a lower resistivity than the resistivity of said silicon substrate;
 - first and second circuit sections formed in said silicon epitaxial layer; and
 - a device isolation region projecting from said silicon substrate up to a surface of each of said first and second circuit sections between said first and second circuit sections.
2. (Previously Presented) The semiconductor integrated circuit according to Claim 1, wherein the resistivity of said silicon substrate is between 20 and 100 times the resistivity of said silicon epitaxial layer.
3. (Previously Presented) The semiconductor integrated circuit according to Claim 2, wherein the resistivity of said silicon substrate is between 50 and 100 times the resistivity of said silicon epitaxial layer.
4. (Canceled)

App. No.: 10/695,969

5. (Original) The semiconductor integrated circuit according to Claim 1, wherein a digital circuit is formed on said first circuit section, and an analog circuit is formed on said second circuit section.

6-10. (Canceled).

11. (New) The semiconductor integrated circuit according to Claim 1, wherein said silicon epitaxial layer is a single layer.